



BYW51/F/G/FP/R-200

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	200 V
$T_j \text{ (max)}$	150 °C
$V_F \text{ (max)}$	0.85 V
$t_{rr} \text{ (max)}$	25 ns

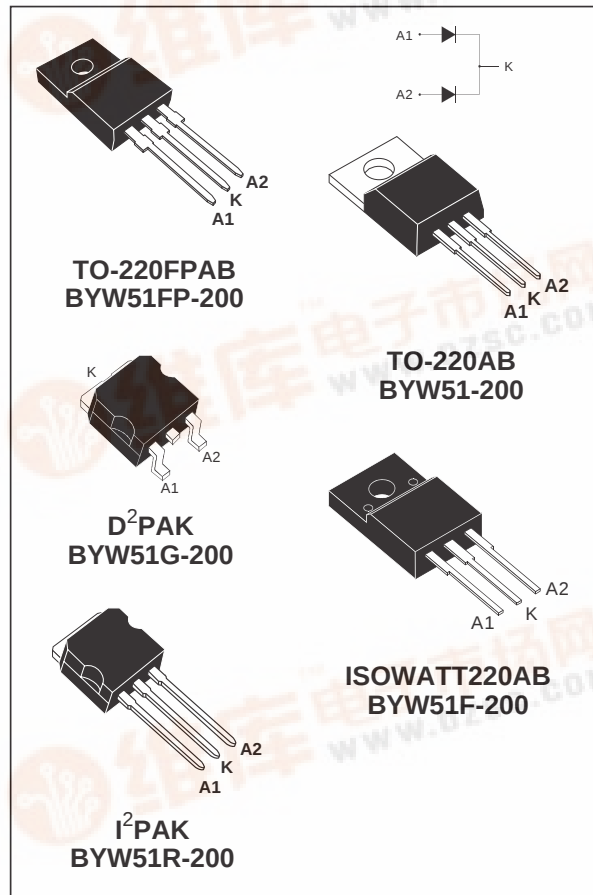
FEATURES AND BENEFITS

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- INSULATED PACKAGES (ISOWATT220AB / TO-220FP):
Insulation voltage = 2000 V DC
Capacitance = 12 pF

DESCRIPTION

Dual center tap rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB, ISOWATT220AB, TO-220FP, D²PAK or I²PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V _{RRM}	Repetitive peak reverse voltage				200	V
I _{F(RMS)}	RMS forward current				20	A
I _{F(AV)}	Average forward current δ = 0.5	TO-220AB / D ² PAK I ² PAK	T _c =120°C	Per diode	10	A
				Per device	20	
		ISOWATT220AB	T _c =95°C	Per diode	10	
				Per device	20	
		TO-220FPAB	T _c =85°C	Per diode	10	
				Per device	20	
I _{FSM}	Surge non repetitive forward current		tp=10ms sinusoidal		100	A
T _{stg}	Storage temperature range				- 65 to + 150	°C
T _j	Maximum operating junction temperature				150	°C

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THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / D ² PAK / I ² PAK	Per diode	2.5	°C/W
			Total	1.4	
		ISOWATT220AB	Per diode	5.1	
			Total	4.05	
		TO-220FPAB	Per diode	5.7	
			Total	4.6	
$R_{th(c)}$	Coupling	TO-220AB / D ² PAK / I ² PAK		0.25	°C/W
		ISOWATT220AB		3.0	
		TO-220FPAB		3.5	

When diodes 1 and 2 are used simultaneously :

$$\Delta T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			15	μA
		$T_j = 100^\circ\text{C}$				1	mA
V_F^{**}	Forward voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 8\text{ A}$			0.85	V
		$T_j = 125^\circ\text{C}$	$I_F = 16\text{ A}$			1.05	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$			1.15	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.025 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Typ.	Max.	Unit
trr	$T_j = 25^\circ\text{C}$	$I_F = 0.5\text{ A}$ $I_R = 1\text{ A}$	$I_{rr} = 0.25\text{ A}$		25	ns
		$I_F = 1\text{ A}$ $V_R = 30\text{ V}$	$dI_F/dt = -50\text{ A}/\mu\text{s}$		35	
tfr	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $V_{FR} = 1.1 \times V_F \text{ max}$	$dI_F/dt = -50\text{ A}/\mu\text{s}$	15		ns
V_{FP}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$	$dI_F/dt = -50\text{ A}/\mu\text{s}$	2		V

Fig. 1: Average forward power dissipation versus average forward current (per diode).

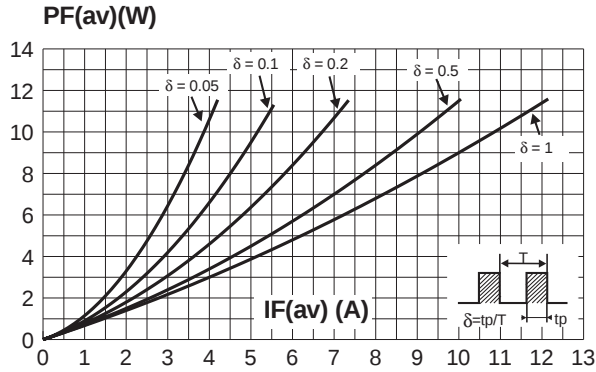


Fig. 2: Peak current versus form factor (per diode).

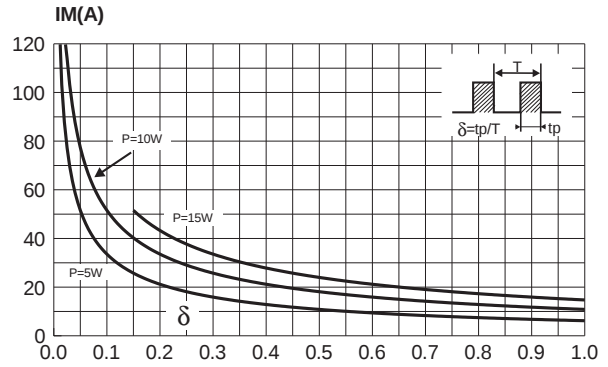


Fig. 3-1: Average forward current versus ambient temperature ($\delta = 0.5$, D²PAK, TO-220AB).

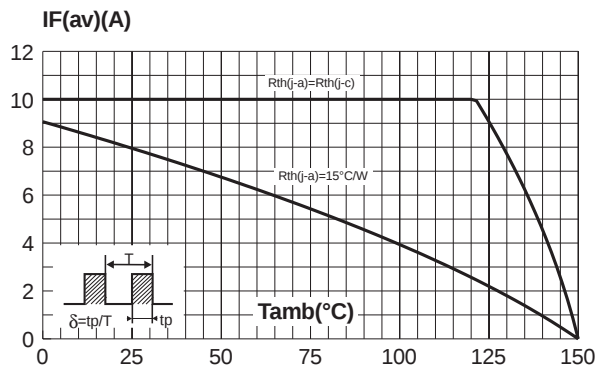


Fig. 3-2: Average forward current versus ambient temperature ($\delta = 0.5$, ISOWATT220AB, TO-220FPAB).

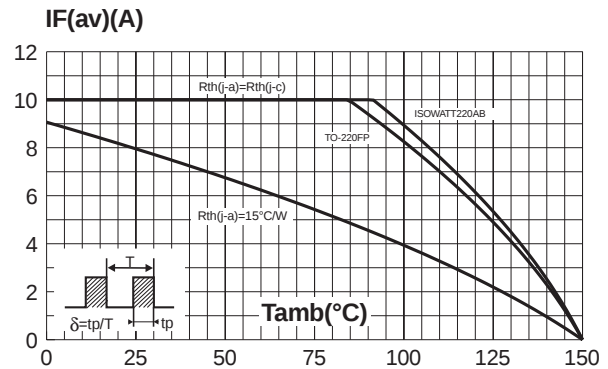


Fig. 4-1: Non repetitive surge peak forward current versus overload duration (D²PAK, TO-220AB).

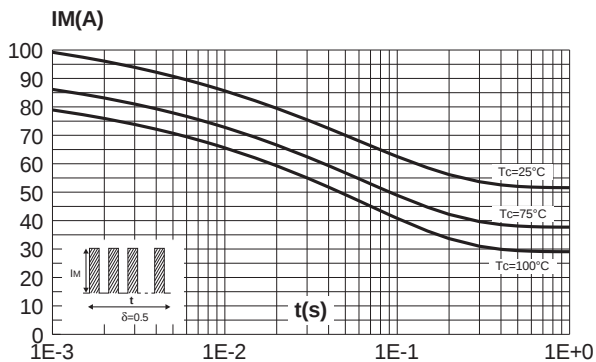


Fig. 4-2: Non repetitive surge peak forward current versus overload duration (ISOWATT220AB).

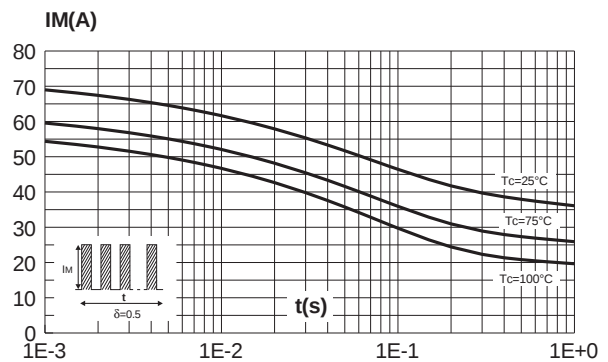


Fig. 4-3: Non repetitive surge peak forward current versus overload duration (TO-220FPAB).

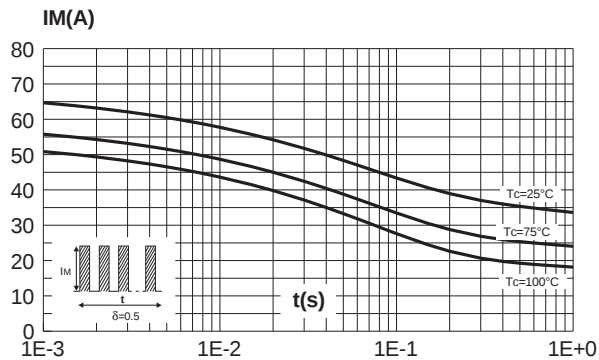


Fig. 5-1: Relative variation of thermal impedance junction to case versus pulse duration (D²PAK, TO-220AB).

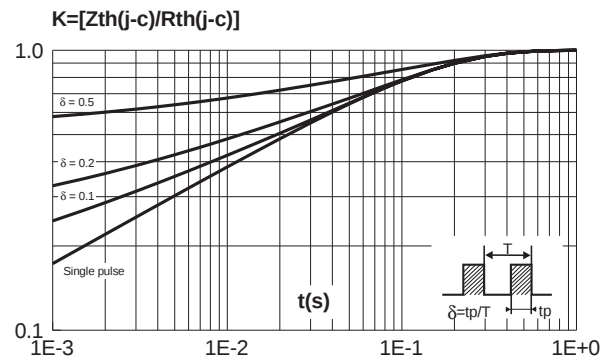


Fig. 5-2: Relative variation of thermal impedance junction to case versus pulse duration (ISOWATT220AB, TO-220FPAB).

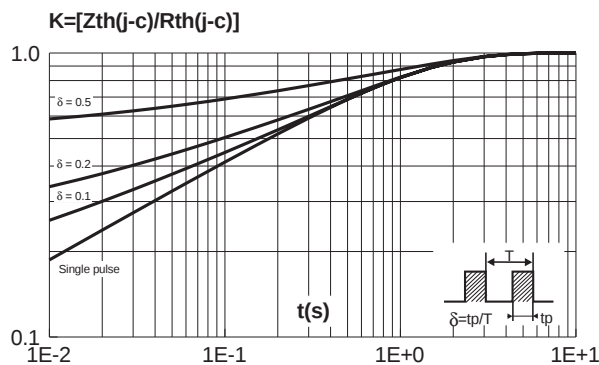


Fig. 6: Forward voltage drop versus forward current (maximum values, per diode).

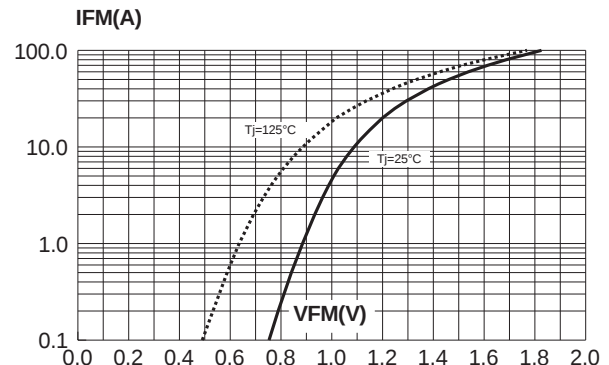


Fig. 7: Junction capacitance versus reverse voltage applied (typical values, per diode).

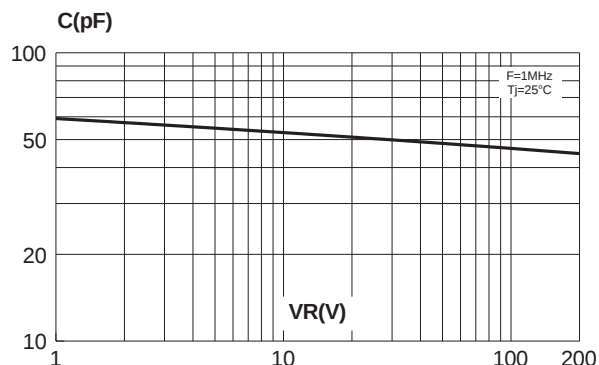


Fig. 8: Reverse recovery charges versus dI_F/dt (per diode).

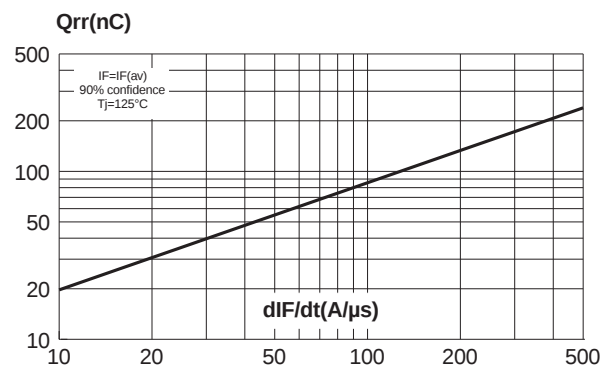


Fig. 9: Peak reverse recovery current versus di_F/dt (per diode).

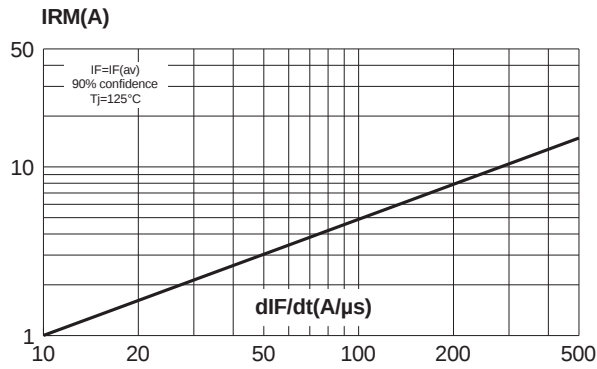


Fig. 10: Dynamic parameters versus junction temperature.

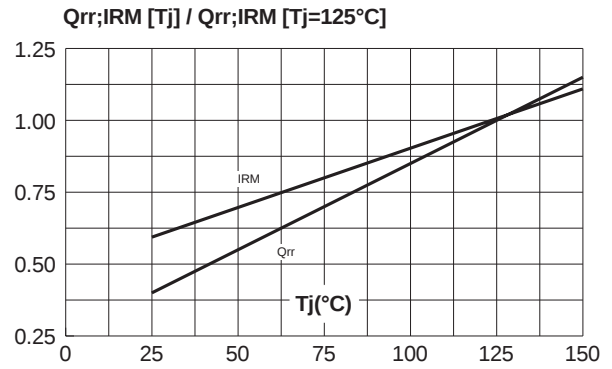
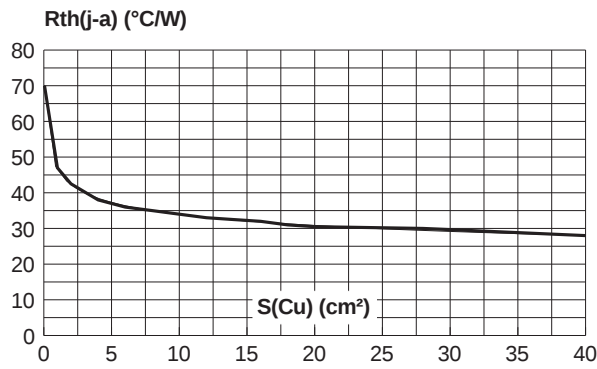
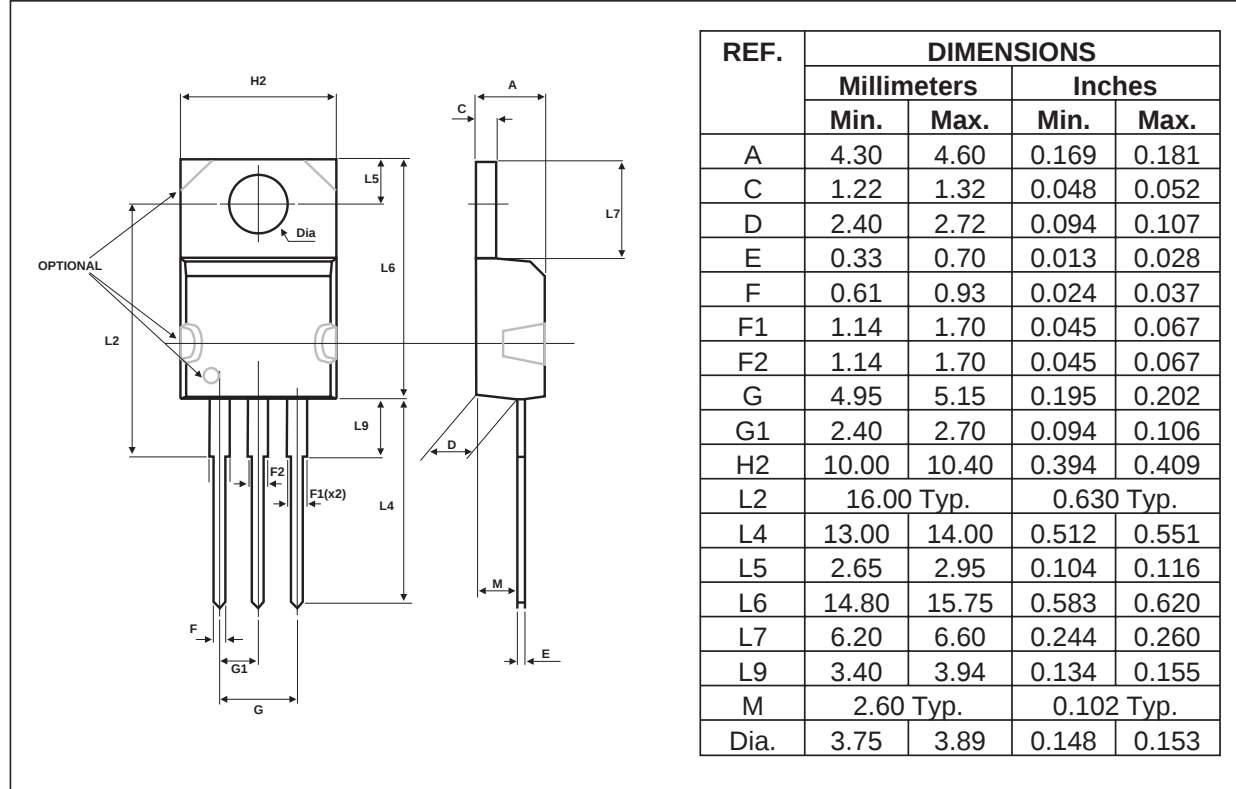


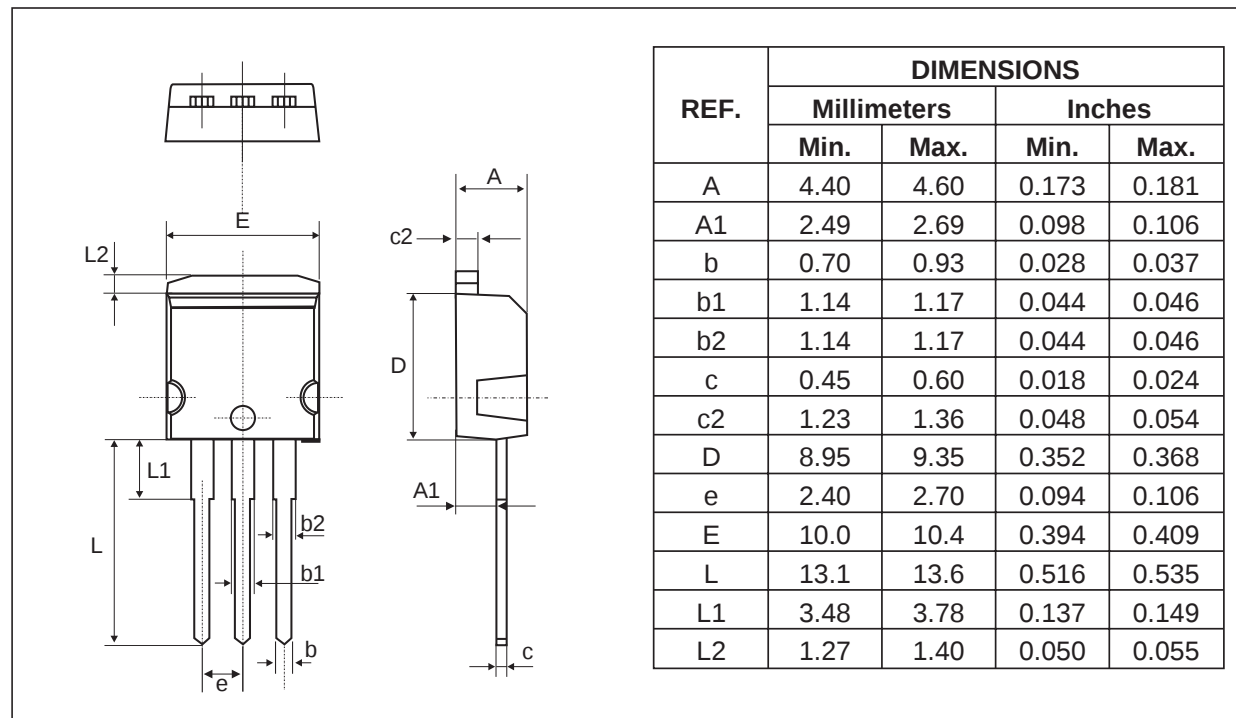
Fig. 11: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: $35\mu m$) (D^2PAK).



PACKAGE MECHANICAL DATA
TO-220AB (JEDEC compatible)

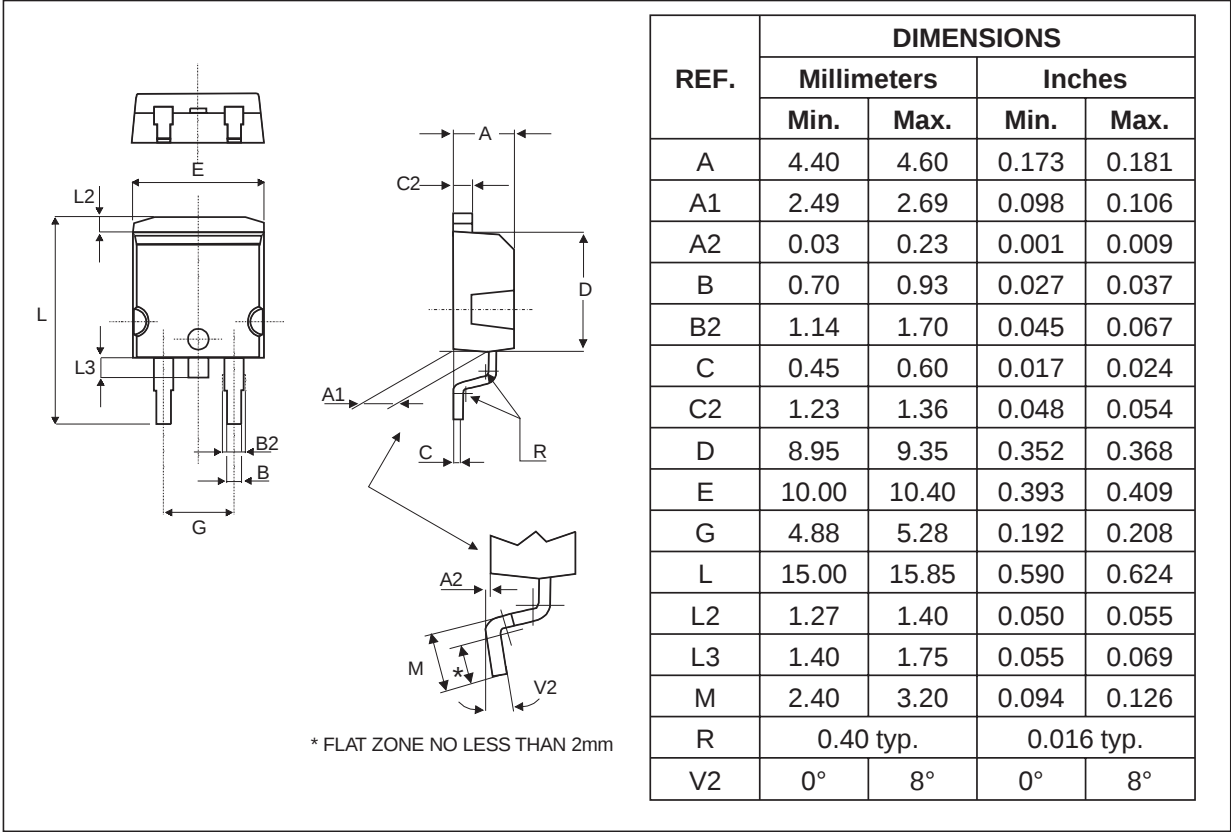


PACKAGE MECHANICAL DATA
I²PAK

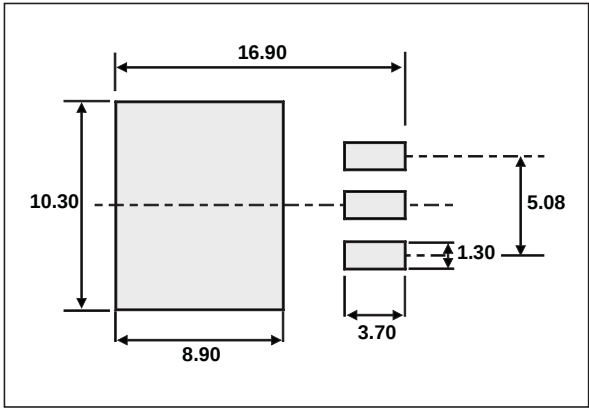


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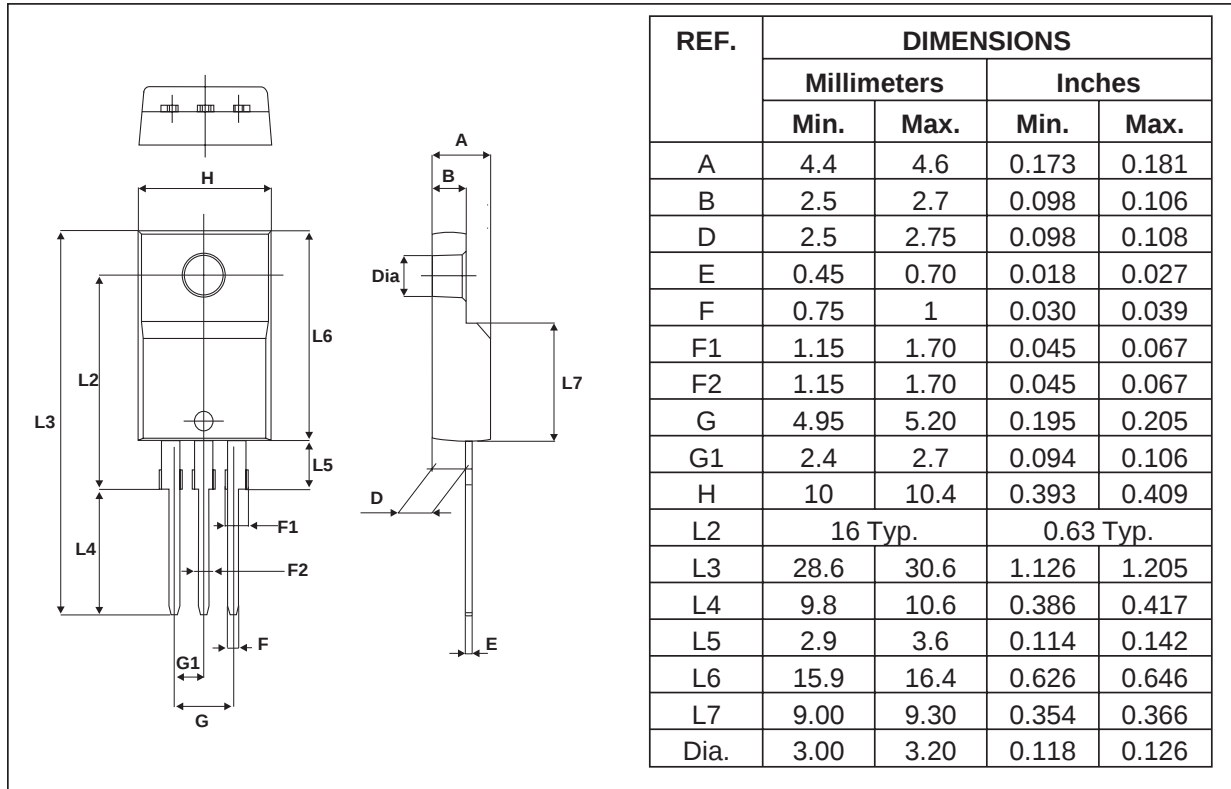
PACKAGE MECHANICAL DATA
D²PAK



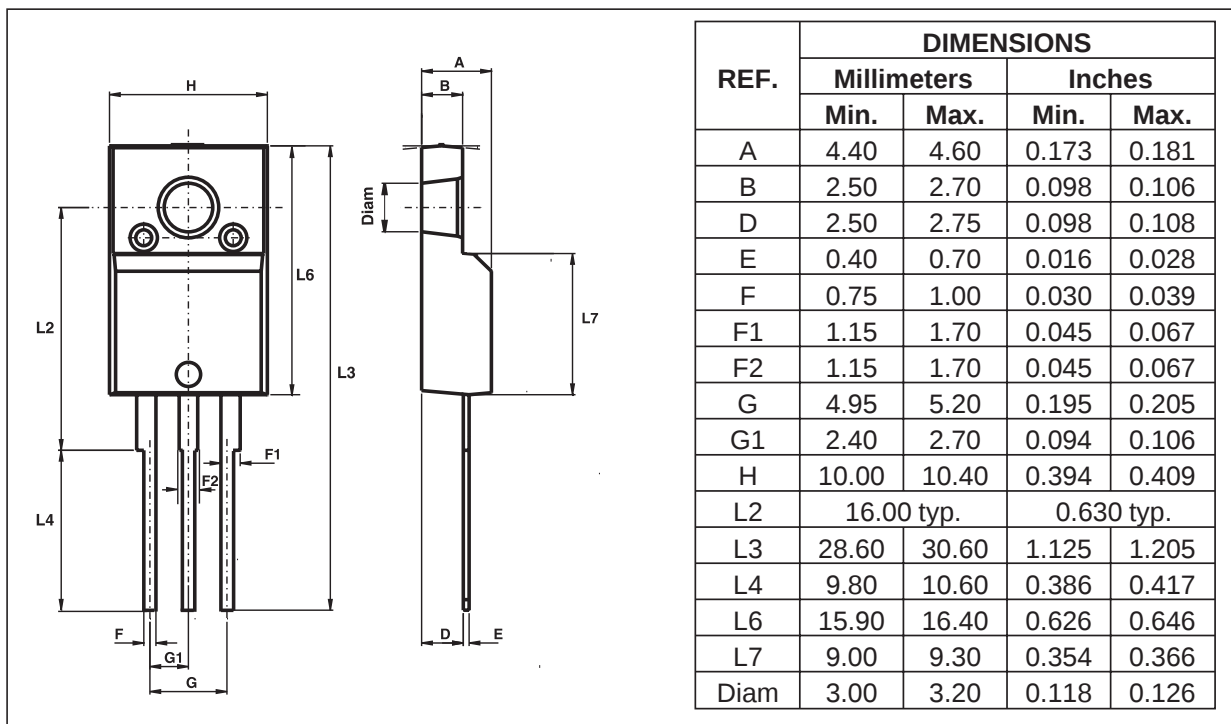
FOOT PRINT (in millimeters)
D²PAK



PACKAGE MECHANICAL DATA
TO-220FPAB



PACKAGE MECHANICAL DATA
ISOWATT220AB (JEDEC compatible)



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW51-200	BYW51-200	TO220AB	2.2 g.	50	Tube
BYW51F-200	BYW51F-200	ISOWATT220AB	2.08 g.	50	Tube
BYW51G-200	BYW51G-200	D ² PAK	1.48 g.	50	Tube
BYW51FP-200	BYW51FP-200	TO-220FPAB	2g	50	Tube
BYW51R-200	BYW51R-200	I ² PAK	1.49 g	50	Tube

- Recommended torque value (TO-220AB): 0.8 N.m.
- Maximum torque value (TO-220AB): 1.0 N.m.
- Recommended torque value (ISOWATT220AB / TO-220FPAB): 0.55 N.m.
- Maximum torque value (ISOWATT220AB / TO-220FPAB): 0.70 N.m.
- Epoxy meets UL94,V0

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